



- ① ((float\$3 adj gate) same (control adj gate)) same (ald (at
(31) ((float\$3 adj gate) same (control adj gate)) and (ald (at
(76436) aluminum adj oxide
(15399) ((barrier near (height tunnel)) ((energy diagram) ne
(10315) work adj function
(24895) (((barrier near (height tunnel)) ((energy diagram) ne
(14) ((float\$3 adj gate) same (control adj gate)) same (alum
(97) ((float\$3 adj gate) same (control adj gate)) same (((ba
(①) ((float\$3 adj gate) same (control adj gate)) same (((ba
(①) ((float\$3 adj gate) same (control adj gate)) same (((ba
(173565) metal adj oxide
(10) (((float\$3 adj gate) same (control adj gate)) same (((ba
(387) ((float\$3 adj gate) same (control adj gate)) and (((ba
(1) (((float\$3 adj gate) same (control adj gate)) and (((ba
(31) ((float\$3 adj gate) same (control adj gate)) and (ald (at
(9) (((barrier adj height) (energy adj band))) near2 (asymme
(41) (((float\$3 adj gate) same (control adj gate)) same (((ba
(49) (((barrier adj height) (energy adj band))) near2 (asymme
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DBs: USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

☒ Plurals

Default operator: OR

☒ Highlight all hit terms initially

(((((barrier adj height) (energy adj band))) near2 (asymmetr\$4 differen\$2)) and (float\$3 adj gate) and (control adj gate)) (((float\$3 adj gate) same (control adj gate)) same (((barrier near (height tunnel)) (energy diagram) near band)) (work adj function))) and (metal adj oxide) (((float\$3 adj gate) same (control adj gate)) and (ald (atomic adj layer adj deposit\$3)))

Dec 2002

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	U	Inventor	Document ID	Issue Date	Page	Title	Current OR	Current XRef	Ret
1	<input checked="" type="checkbox"/>	Faraone, Lorenzo	US 4757360 A	19880712	6	Floating gate memory device with facing asperities on floating and control gates	257/317	257/900; 257/E29.304	
2	<input type="checkbox"/>	Kan, Edwin C. et al.	US 20020192949 A1	20021219	14	Embedded metal nanocrystals	438/652	438/660	
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5	<input checked="" type="checkbox"/>	Lee, Woo-Hyeong et al.	US 5923056 A	19990713	6	Electronic components with doped metal oxide dielectric materials and a process for making electronic components with doped metal oxide	257/192	257/410; 257/411;	
6	<input checked="" type="checkbox"/>	Muralidhar, Ramachandran et al.	US 6320784 B1	20011120	7	Memory cell and method for programming thereof	365/151	257/E29.301; 257/E29.308;	
7	<input checked="" type="checkbox"/>	Nguyen, Bich-Yen et al.	US 20020137250 A1	20020926	10	High K dielectric film and method for making	438/53		
8	<input checked="" type="checkbox"/>	Uchida, Hidetsugu	US 6229175 B1	20010508	24	Nonvolatile memory	257/315	257/298; 257/316	